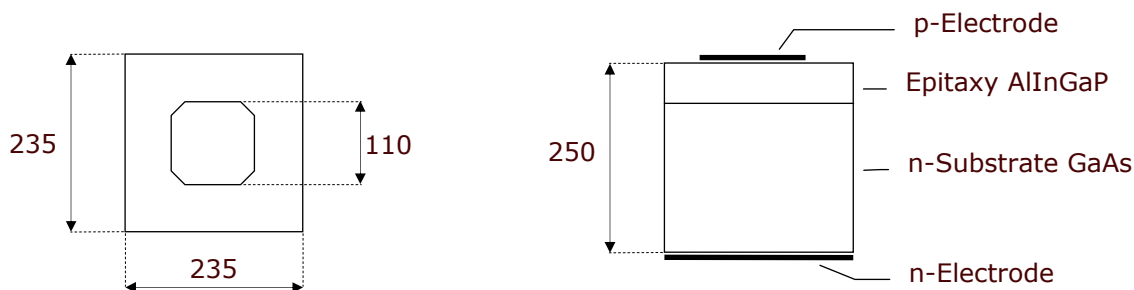


**YELLOW-GREEN**

**Item No.: 160272**

1. This specification applies to AlInGaP / GaAs LED Chips
2. Structure
  - 2.1 Mesa structure
  - 2.2 Electrodes
 

|                  |                |
|------------------|----------------|
| p-side (anode)   | Au alloy or Al |
| n-side (cathode) | Au alloy       |
3. Outlines (dimensions in microns)



Wire bond contacts can also be square

4. Electrical and optical characteristics (T=25°C)

| Parameter            | Symbol      | Conditions            | min | typ  | max  | Unit          |
|----------------------|-------------|-----------------------|-----|------|------|---------------|
| Forward voltage      | $V_F$       | $I_F = 20 \text{ mA}$ |     | 2,10 | 2,40 | V             |
| Reverse current      | $I_R$       | $V_R = 5 \text{ V}$   |     |      | 10   | $\mu\text{A}$ |
| Luminous intensity * | $I_V$       | $I_F = 10 \text{ mA}$ |     | 26,0 |      | mcd           |
| dom. wavelength      | $\lambda_D$ | $I_F = 20 \text{ mA}$ |     | 572  |      | nm            |

\* On request, wafers will be delivered according to luminous intensity classes  
Brightness measurement at OSA on gold plate

5. Packing

Dice on adhesive film with 1) wire bond side on top  
2) back contact on top

6. Labeling

| Type | Lot No. | $I_V$ typ<br>min<br>max | Quantity |
|------|---------|-------------------------|----------|
|------|---------|-------------------------|----------|